

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
		(etch\$ near10 (metal near5 ions)) and ("chemical mechanical")	USPAT; EPO; JPO; DERWENT	OR	OFF	2002/07/23 15:07
		(etch\$ near5 (metal near5 ions)) and ("chemical mechanical")	USPAT; EPO; JPO; DERWENT	OR	OFF	2002/07/23 15:07
L1	4	"0761387"	EPO; DERWENT	OR	ON	2005/09/19 11:10
L2	0	"0 761387"	EPO; DERWENT	OR	ON	2005/09/19 11:10
L3	7	"761387"	EPO; DERWENT	OR	ON	2005/09/19 11:10
S1	103410	polish\$3 or abrad\$3 or CMP or "chemical mechanical polishing" or "chemical mechanical planarization"	USPAT	OR	ON	2005/09/16 13:34
S2	25434	(polish\$3 or abrad\$3 or CMP or "chemical mechanical polishing" or "chemical mechanical planarization") and (wafer semiconductor ic "integrate circuit")	USPAT	OR	ON	2001/09/18 12:42
S3	1371	((polish\$3 or abrad\$3 or CMP or "chemical mechanical polishing" or "chemical mechanical planarization") and (wafer semiconductor ic "integrate circuit")) and (156/345 or "441"/\$ or "216"/\$).ccls.	USPAT	OR	ON	2001/09/18 12:42
S4	19730	(156/345 or "441"/\$ or "216"/\$).ccls.	USPAT	OR	ON	2001/09/18 12:42
S5	45238	(polish\$3 or abrad\$3 or CMP or "chemical mechanical polishing" or "chemical mechanical planarization") and (wafer semiconductor ic "integrate circuit") or ((156/345 or "441"/\$ or "216"/\$).ccls.)	USPAT	OR	ON	2001/09/18 12:44
S6	45238	((polish\$3 or abrad\$3 or CMP or "chemical mechanical polishing" or "chemical mechanical planarization") and (wafer semiconductor ic "integrate circuit"))or ((156/345 or "441"/\$ or "216"/\$).ccls.)	USPAT	OR	ON	2001/09/18 12:43

S7	5121	((polish\$3 or abrad\$3 or CMP or "chemical mechanical polishing" or "chemical mechanical planarization") and (wafer semiconductor ic "integrate circuit") or ((156/345 or "441"/\$ or "216"/\$).ccls.)) and (etch near10 (metal or ion))	USPAT	OR	ON	2001/09/18 12:46
S8	491	((polish\$3 or abrad\$3 or CMP or "chemical mechanical polishing" or "chemical mechanical planarization") and (wafer semiconductor ic "integrate circuit") or ((156/345 or "441"/\$ or "216"/\$).ccls.)) and (clean\$3 and scrubb\$3)) and etch\$3	USPAT	OR	ON	2001/09/18 12:48
S9	749	((polish\$3 or abrad\$3 or CMP or "chemical mechanical polishing" or "chemical mechanical planarization") and (wafer semiconductor ic "integrate circuit") or ((156/345 or "441"/\$ or "216"/\$).ccls.)) and (clean\$3 and scrubb\$3)	USPAT	OR	ON	2005/03/15 15:57
S10	0	sotozaki-\$in.	USPAT	OR	ON	2001/09/18 12:58
S11	392	haneda-\$in.	USPAT	OR	ON	2001/09/18 13:10
S12	0	asahicho-\$in.	USPAT	OR	ON	2001/09/18 13:00
S13	67	hiroshi-\$in.	USPAT	OR	ON	2001/09/18 13:00
S14	24	koji-\$in.	USPAT	OR	ON	2001/09/18 13:05
S15	12	ato-\$in.	USPAT	OR	ON	2001/09/18 13:06
S16	677	ebara.as.	USPAT	OR	ON	2001/09/18 13:10
S17	279	ebara.as. and (semiconductor wafer substrate)	USPAT	OR	ON	2001/09/18 13:10
S18	139	((polish\$3 or abrad\$3 or CMP or "chemical mechanical polishing" or "chemical mechanical planarization") and (wafer semiconductor ic "integrate circuit") or ((156/345 or "441"/\$ or "216"/\$).ccls.)) and (clean\$3 and scrubb\$3)) and (rotat\$5 turntable)same clean	USPAT	OR	ON	2001/09/20 17:03
S19	49254	(polish\$3 or abrad\$3 or CMP or "chemical mechanical polishing" or "chemical mechanical planarization") and (wafer semiconductor ic "integrate circuit") or (156/345 or "441"/\$ or "216"/\$).ccls.)	USPAT	OR	ON	2001/09/20 17:16

S20	9248	((polish\$3 or abrad\$3 or CMP or "chemical mechanical polishing" or "chemical mechanical planarization") and (wafer semiconductor ic "integrate circuit") or (156/345 or "441"/\$ or "216"/\$.ccls.)) and (computer or controller)	USPAT	OR	ON	2001/09/20 17:17
S21	8332	((((polish\$3 or abrad\$3 or CMP or "chemical mechanical polishing" or "chemical mechanical planarization") and (wafer semiconductor ic "integrate circuit") or (156/345 or "441"/\$ or "216"/\$.ccls.)) and (computer or controller)) and (time)	USPAT	OR	ON	2001/09/20 17:17
S22	2872	time same (computer or controller) and ((polish\$3 or abrad\$3 or CMP or "chemical mechanical polishing" or "chemical mechanical planarization") and (wafer semiconductor ic "integrate circuit") or (156/345 or "441"/\$ or "216"/\$.ccls.))	USPAT	OR	ON	2001/09/20 17:18
S23	189	clean\$3 same time same (computer or controller) and ((polish\$3 or abrad\$3 or CMP or "chemical mechanical polishing" or "chemical mechanical planarization") and (wafer semiconductor ic "integrate circuit") or (156/345 or "441"/\$ or "216"/\$.ccls.))	USPAT	OR	ON	2001/09/20 17:19
S24	15397	chemical adj mechanical	USPAT	OR	OFF	2002/07/22 13:35
S25	9580	(chemical adj mechanical) adj (polishing planarization)	USPAT	OR	OFF	2002/07/22 13:35
S26	585	((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water	USPAT	OR	OFF	2005/03/15 15:57
S27	188	((((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water) and (scrubbing scrubber scrub)	USPAT	OR	OFF	2002/07/22 13:59

S28	3780	(((chemical adj mechanical) adj (polishing planarization)) (((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water) (((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water) and (scrubbing scrubber scrub)) ((((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water) and (scrubbing scrubber scrub)) and (spin?dry))) and (etch\$3 same ion)	USPAT	OR	ON	2002/07/22 13:39
S29	0	(((chemical adj mechanical) adj (polishing planarization)) (((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water) (((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water) and (scrubbing scrubber scrub)) ((((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water) and (scrubbing scrubber scrub)) and (spin?dry))) and (etch\$3 same ion)) and (primary and secondary)near5 ((cleaning cleaner) and (polishing polish polisher))	USPAT	OR	ON	2002/07/22 13:42
S30	5	(((chemical adj mechanical) adj (polishing planarization)) (((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water) (((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water) and (scrubbing scrubber scrub)) ((((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water) and (scrubbing scrubber scrub)) and (spin?dry))) and (etch\$3 same ion)) and (primary and secondary)near5 ((cleaning cleaner) or (polishing polish polisher))	USPAT	OR	ON	2002/07/22 13:42

S31	127	(((chemical adj mechanical) adj (polishing planarization)) (((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water) (((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water) and (scrubbing scrubber scrub)) ((((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water) and (scrubbing scrubber scrub)) and (spin?dry))) and (etch\$3 same ion)) and (primary and secondary)	USPAT	OR	ON	2002/07/22 13:46
S32	185	(((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water) and (scrubbing scrubber scrub)) not (((((chemical adj mechanical) adj (polishing planarization)) (((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water) (((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water) and (scrubbing scrubber scrub)) ((((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water) and (scrubbing scrubber scrub)) and (spin?dry))) and (etch\$3 same ion)) and (primary and secondary))	USPAT	OR	OFF	2002/07/23 14:29
S33	12	(((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water) and (scrubbing scrubber scrub)) and (spin?dry)	USPAT	OR	OFF	2002/07/23 08:24

S34	195	(((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water) and (scrubbing scrubber scrub)) not (((chemical adj mechanical) adj (polishing planarization)) ((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water) (((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water) and (scrubbing scrubber scrub)) (((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water) and (scrubbing scrubber scrub)) and (spin?dry))) and (etch\$3 same ion)) and (primary and secondary))	USPAT; EPO; JPO; DERWENT	OR	OFF	2002/07/23 14:41
S35	175	clean\$3 same etch\$3 same scrub\$3	USPAT; EPO; JPO; DERWENT	OR	OFF	2002/07/23 14:42
S36	51	(clean\$3 same etch\$3 same scrub\$3) and (polish\$ planariz\$5)	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/15 15:56
S37	5	((etch\$ near10 (metal near5 ions)) and ("chemical mechanical")) not ((etch\$ near5 (metal near5 ions)) and ("chemical mechanical"))	USPAT; EPO; JPO; DERWENT	OR	OFF	2002/07/23 15:06
S38	6	((etching etch) near5 (metal near5 ions)) and ("chemical mechanical")	USPAT; EPO; JPO; DERWENT	OR	OFF	2002/07/23 15:08
S39	0	(((etching etch) near5 (metal near5 ions)) and ("chemical mechanical")) not (((etch\$ near5 (metal near5 ions)) and ("chemical mechanical")) ((etch\$ near10 (metal near5 ions)) and ("chemical mechanical"))))	USPAT; EPO; JPO; DERWENT	OR	OFF	2002/07/23 15:08
S40	20	((etching etch) near5 (metal near5 ions)) and (polishig polish planariz\$5)	USPAT; EPO; JPO; DERWENT	OR	OFF	2002/07/23 15:09
S41	35	((etching etch) near5 (metal near5 ions)) and (polishing polish planariz\$5)	USPAT; EPO; JPO; DERWENT	OR	OFF	2002/07/23 15:09
S42	35	(((etching etch) near5 (metal near5 ions)) and (polishig polish planariz\$5)) (((etching etch) near5 (metal near5 ions)) and (polishing polish planariz\$5))	USPAT; EPO; JPO; DERWENT	OR	OFF	2002/07/23 15:09

S43	29	(((((etching etch) near5 (metal near5 ions)) and (polishig polish planariz\$5)) (((etching etch) near5 (metal near5 ions)) and (polishing polish planariz\$5)))) not (((etch\$ near5 (metal near5 ions)) and ("chemical mechanical"))) ((etch\$ near10 (metal near5 ions)) and ("chemical mechanical"))))	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/15 15:57
S56	0	ep0774323.ipc.	EPO	OR	ON	2005/03/15 15:54
S57	0	"0774323"	EPO	OR	ON	2005/03/15 15:54
S58	0	"00774323"	EPO	OR	ON	2005/03/15 15:54
S59	0	"7743230"	EPO	OR	ON	2005/03/15 15:54
S60	0	"ep-7743230"	EPO	OR	ON	2005/03/15 15:54
S61	0	ep-7743230	EPO	OR	ON	2005/03/15 15:54
S62	0	ep-07743230	EPO	OR	ON	2005/03/15 15:54
S63	31	perlov-\$in.	EPO	OR	ON	2005/03/15 15:55
S64	105	(clean\$3 same etch\$3 same scrub\$3) and (polish\$ planariz\$5)	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/15 15:56
S65	1166	((polish\$3 or abrad\$3 or CMP or "chemical mechanical polishing" or "chemical mechanical planarization") and (wafer semiconductor ic "integrate circuit") or ((156/345 or "441"/\$ or "216"/\$).ccls.)) and (clean\$3 and scrubb\$3)	USPAT	OR	ON	2005/03/15 15:57
S66	1168	((chemical adj mechanical) adj (polishing planarization)) and (cleaning cleaner) same water	USPAT	OR	OFF	2005/03/15 15:57
S67	35	(((((etching etch) near5 (metal near5 ions)) and (polishig polish planariz\$5)) (((etching etch) near5 (metal near5 ions)) and (polishing polish planariz\$5)))) not (((etch\$ near5 (metal near5 ions)) and ("chemical mechanical"))) ((etch\$ near10 (metal near5 ions)) and ("chemical mechanical"))))	USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/15 15:57
S68	85052	(edge contact retain\$3)near2 ring	USPAT	OR	ON	2005/03/15 16:33
S69	1514	S68 with (wafer semiconductor)	USPAT	OR	ON	2005/03/15 16:33
S70	119	S69 with (silicon elastomer)	USPAT	OR	ON	2005/03/15 17:01
S71	60	S70 same (vacuum suction water)	USPAT	OR	ON	2005/03/15 16:44
S72	96	zuniga-\$in.	USPAT	OR	ON	2005/03/15 16:45
S73	55	S72 and (water vacuum)	USPAT	OR	ON	2005/03/15 16:46

S74	2	S72 and (water vacuum)with (aperture\$1 hole\$1 pore\$1)	USPAT	OR	ON	2005/03/15 16:48
S75	2	S74 and S68	USPAT	OR	ON	2005/03/15 16:48
S76	85052	(edge contact retain\$3)near2 ring	USPAT	OR	ON	2005/03/15 17:01
S77	1514	S76 with (wafer semiconductor)	USPAT	OR	ON	2005/03/15 17:01
S78	119	S77 with (silicon elastomer)	USPAT	OR	ON	2005/03/15 17:01
S79	90	S78 and plate	USPAT	OR	ON	2005/03/15 17:01
S80	5	S78 same plate	USPAT	OR	ON	2005/03/15 17:01
S81	210335	polish\$3 or abrad\$3 or CMP or "chemical mechanical polishing" or "chemical mechanical planarization"	US-PGPUB; USPAT	OR	ON	2005/09/16 13:35
S82	212432	(clean\$3 wash\$3 rins\$3 etch\$3) with (substrate wafer semiconductor)	US-PGPUB; USPAT	OR	ON	2005/09/16 13:36
S83	23381	S81 same S82	US-PGPUB; USPAT	OR	ON	2005/09/16 13:36
S84	14932	S81 with S82	US-PGPUB; USPAT	OR	ON	2005/09/16 13:36
S85	12502	118/719 156/345.31 156/345.32 216/53 (216/88-91).ccls. 451/28 451/66 134/1.3 134/108 134/84 438/8 438/692	US-PGPUB; USPAT	OR	ON	2005/09/16 13:38
S86	1943	S84 and S85	US-PGPUB; USPAT	OR	ON	2005/09/16 13:38
S87	188000	(first and second) near5 (wafer semiconductor substrate)	US-PGPUB; USPAT	OR	ON	2005/09/16 13:39
S88	189062	S86 S87	US-PGPUB; USPAT	OR	ON	2005/09/16 13:39
S89	881	S86 and S87	US-PGPUB; USPAT	OR	ON	2005/09/16 13:39
S90	4486	clean\$3 with (polish\$3) with (wafer semiconductor substrate)	US-PGPUB; USPAT	OR	ON	2005/09/16 13:40
S91	849	S85 and S90	US-PGPUB; USPAT	OR	ON	2005/09/16 13:40
S92	1316	S89 S91	US-PGPUB; USPAT	OR	ON	2005/09/16 13:40